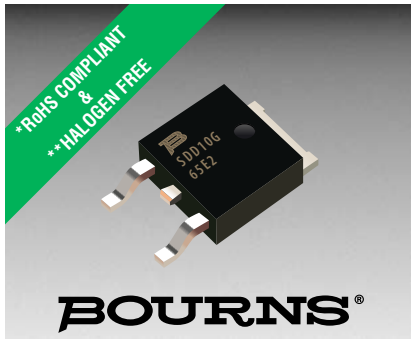




## Features

- High efficiency with low power loss
- Low reverse leakage current
- High peak forward surge current ( $I_{FSM}$ )
- Reduced EMI
- Maximum operating  $T_J$  up to 175 °C
- Epoxy compound is flame retardant to the UL 94V-0 standard
- RoHS compliant\*, Pb free and halogen free\*\*

## Applications

- Switched-Mode Power Supplies (SMPS)
- Power Factor Correction (PFC)
- PV inverters
- DC-DC converters
- Telecommunications
- Motor drives

# BSDD10G65E2 Silicon Carbide Schottky Diode

## General Information

Bourns® Model BSDD10G65E2 Silicon Carbide (SiC) Schottky Diode provides excellent current carrying capacity. This advanced, high efficiency power component is suitable for applications such as converters requiring a high peak forward surge capability, a very low forward voltage drop, reduced thermal resistance and low power loss.

Bourns offers Silicon Carbide Schottky Diodes for rectification applications in assorted styles. The Model BSDD10G65E2 is available in a TO252 (DPAK) package, well-suited for high frequency Switched-Mode Power Supplies.

## Additional Information

Click these links for more information:



## Absolute Maximum Ratings (@ $T_J = 25\text{ °C}$ Unless Otherwise Noted)

| Parameter                                                                                                                                                         | Symbol      | BSDD10G65E2 | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|-------------|------|
| Repetitive Peak Reverse Voltage                                                                                                                                   | $V_{RRM}$   | 650         | V    |
| Average Forward Current<br>(Square Wave Pulse, $D = 0.5$ , $T_{mb} \leq 140\text{ °C}$ , <a href="#">Fig. Zth(J-mb)</a> )                                         | $I_{F(AV)}$ | 10          | A    |
| Repetitive Peak Forward Current<br>(Square Wave Pulse, $D = 0.5$ , $T_{mb} \leq 140\text{ °C}$ , $t_p = 25\text{ }\mu\text{s}$ , <a href="#">Fig. Zth(J-mb)</a> ) | $I_{FRM}$   | 20          | A    |
| Non-Repetitive Peak Forward Surge Current<br>(10 ms, Single Sine-Wave Pulse)                                                                                      | $I_{FSM}$   | 55          | A    |
| Total Power Dissipation                                                                                                                                           | $P_{tot}$   | 136.3       | W    |
| Operating Junction Temperature Range                                                                                                                              | $T_J$       | -55 to +175 | °C   |
| Storage Temperature                                                                                                                                               | $T_{STG}$   | -55 to +175 | °C   |

## Thermal Characteristics

| Parameter          | Symbol             | Condition or Model                 | Min. | Typ. | Max. | Unit |
|--------------------|--------------------|------------------------------------|------|------|------|------|
| Thermal Resistance | $R_{\theta(J-A)}$  | In ambient air                     |      | 50   |      | °C/W |
|                    | $R_{\theta(J-mb)}$ | Transient thermal impedance curves |      | 0.9  | 1.1  |      |

## Electrical Characteristics (@ $T_J = 25\text{ °C}$ Unless Otherwise Noted)

| Parameter                 | Symbol | Condition or Model                                                                          | Min. | Typ.        | Max.       | Unit          |
|---------------------------|--------|---------------------------------------------------------------------------------------------|------|-------------|------------|---------------|
| Forward Voltage           | $V_F$  | $I_F = 10\text{ A}$ , $T_J = 25\text{ °C}$<br>$I_F = 10\text{ A}$ , $T_J = 175\text{ °C}$   |      | 1.45<br>2.0 | 1.7<br>2.3 | V             |
| Reverse Leakage Current   | $I_R$  | $V_R = 650\text{ V}$ , $T_J = 25\text{ °C}$<br>$V_R = 650\text{ V}$ , $T_J = 175\text{ °C}$ |      | 0.5<br>25   | 50<br>250  | $\mu\text{A}$ |
| Recovered Charge          | $Q_r$  | $dI_F/dt = 500\text{ A}/\mu\text{s}$ , $V_R = 400\text{ V}$ , $I_F = 10\text{ A}$           |      | 14.5        |            | nC            |
| Diode Capacitance         | $C_d$  | $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$                                                     |      | 323         |            | pF            |
| Capacitance Stored Energy | $E_c$  | $V_R = 400\text{ V}$                                                                        |      | 3.4         |            | $\mu\text{J}$ |



**WARNING Cancer and Reproductive Harm - [www.P65Warnings.ca.gov](http://www.P65Warnings.ca.gov)**

\*RoHS Directive 2015/863, Mar 31, 2015 and Annex.

\*\*Bourns considers a product to be "halogen free" if (a) the Bromine (Br) content is 900 ppm or less; (b) the Chlorine (Cl) content is 900 ppm or less; and (c) the total Bromine (Br) and Chlorine (Cl) content is 1500 ppm or less.

Specifications are subject to change without notice.

Users should verify actual device performance in their specific applications.

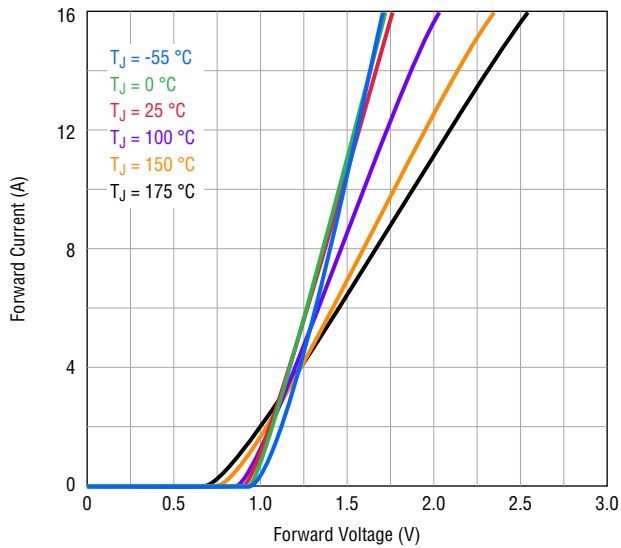
The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

# BSDD10G65E2 Silicon Carbide Schottky Diode

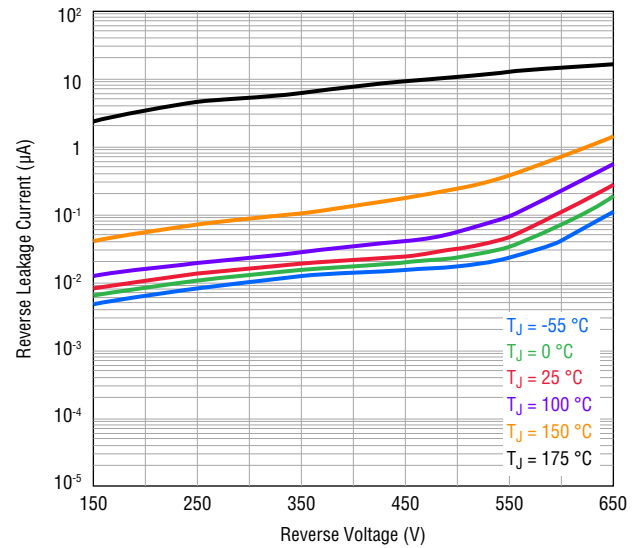
**BOURNS®**

Rating and Characteristic Curves ( $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted)

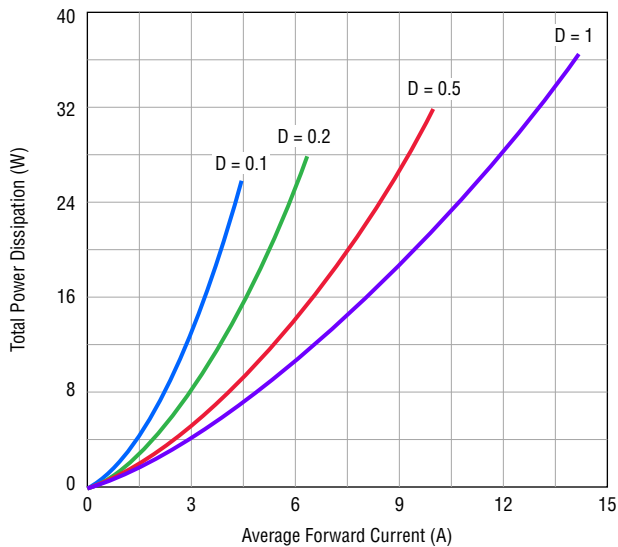
Typical Forward Characteristics



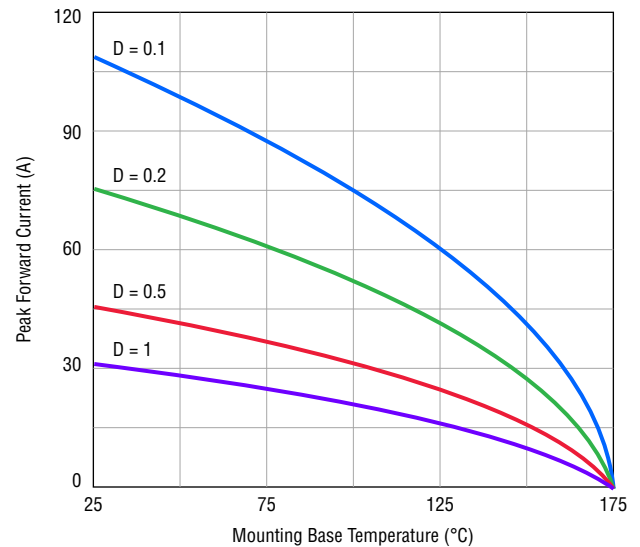
Typical Reverse Characteristics



Forward Power Dissipation



Forward Current Derating



Specifications are subject to change without notice.

Users should verify actual device performance in their specific applications.

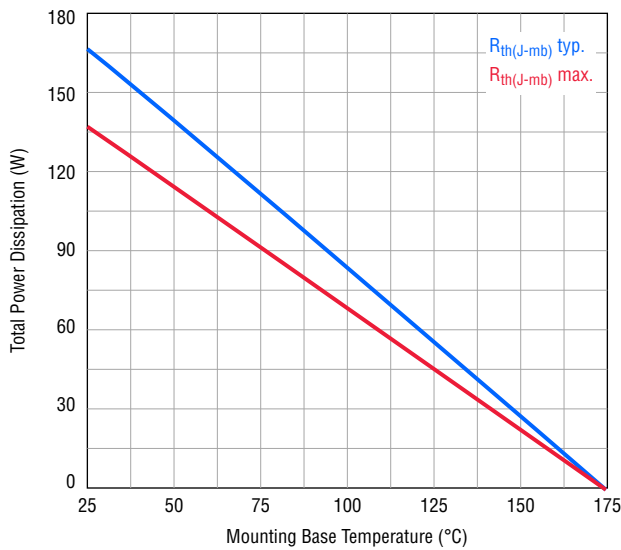
The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

# BSDD10G65E2 Silicon Carbide Schottky Diode

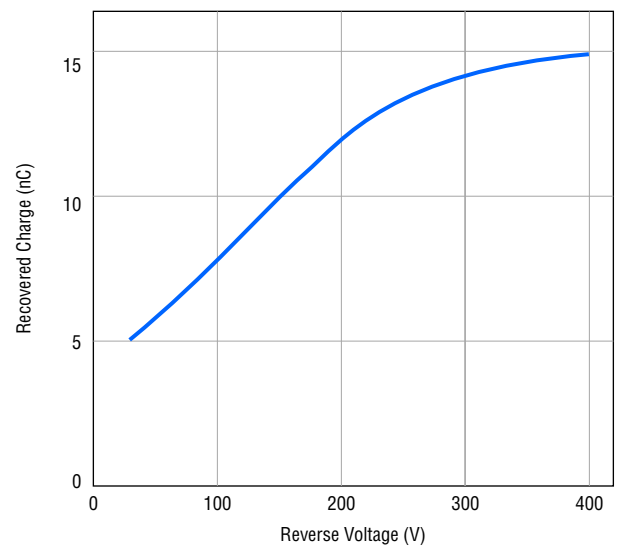
**BOURNS®**

## Rating and Characteristic Curves (Continued)

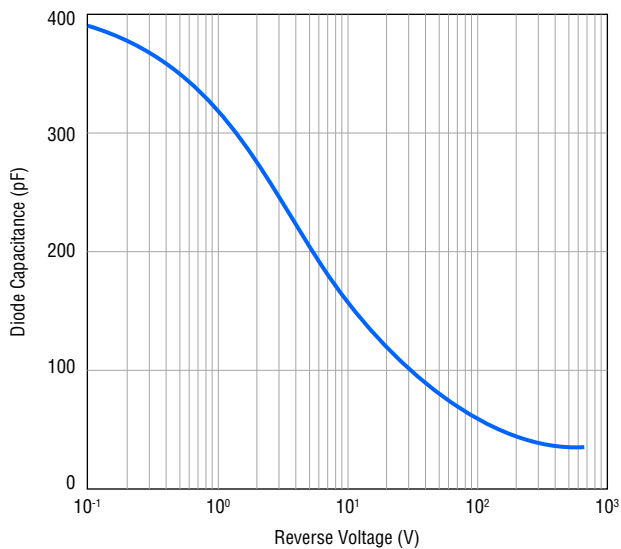
### Power Derating



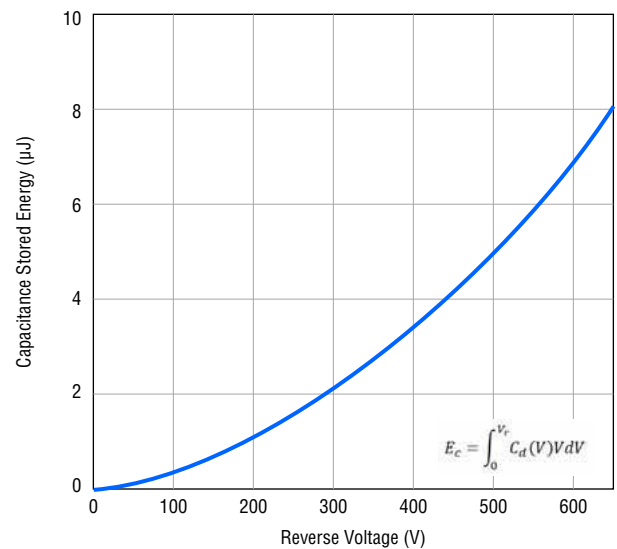
### Typical Recovered Charge vs $V_R$



### Typical Diode Capacitance vs $V_R$



### Typical Capacitance Stored Energy vs $V_R$



Specifications are subject to change without notice.

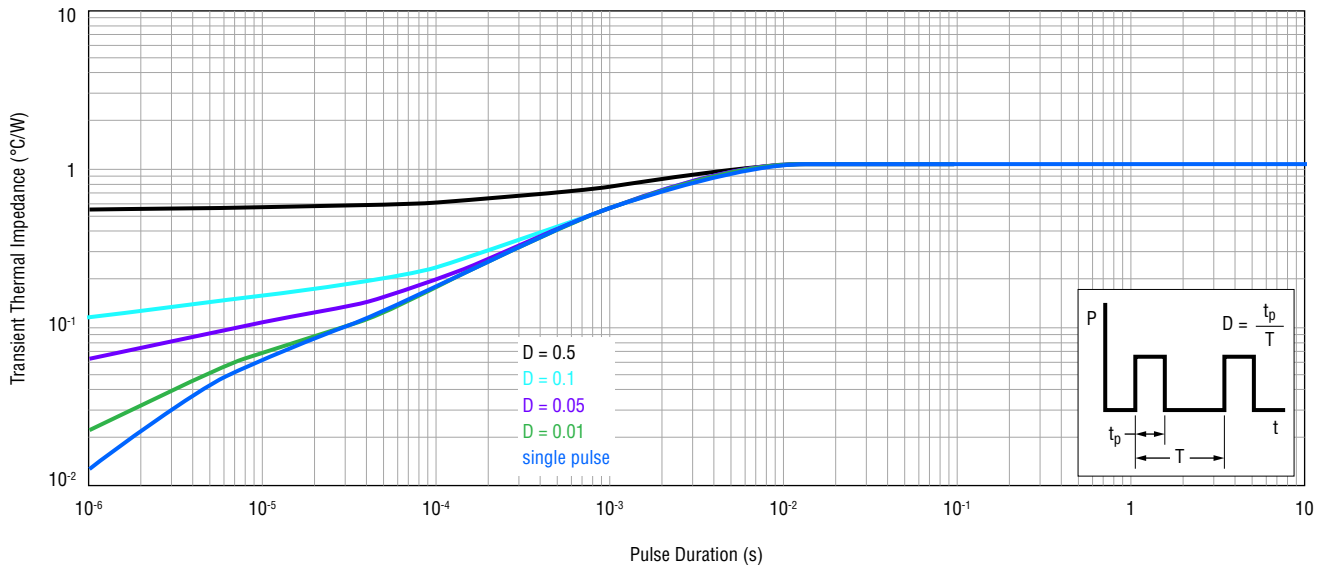
Users should verify actual device performance in their specific applications.

The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

# BSDD10G65E2 Silicon Carbide Schottky Diode

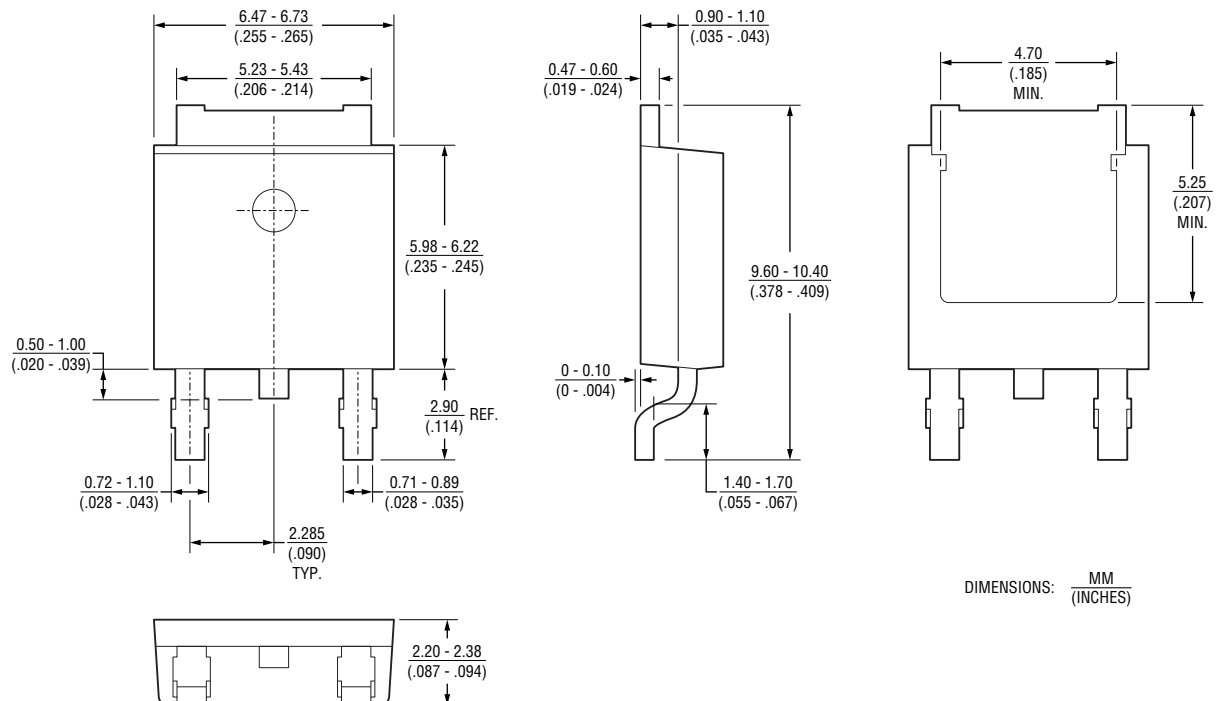
**BOURNS®**

## Transient Thermal Impedance, $Z_{th(J-mb)}$



## Product Dimensions

Package: TO252 (DPAK)



Specifications are subject to change without notice.

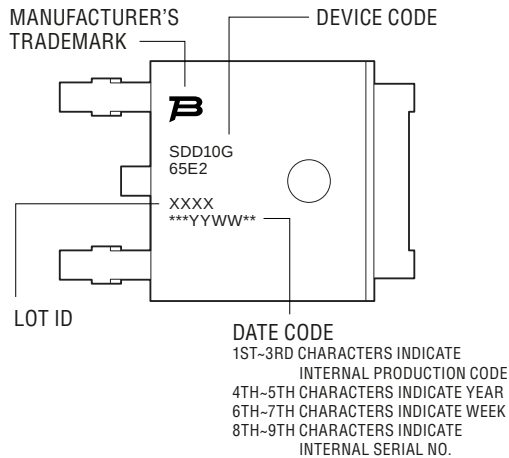
Users should verify actual device performance in their specific applications.

The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

# BSDD10G65E2 Silicon Carbide Schottky Diode

**BOURNS®**

## Typical Part Marking



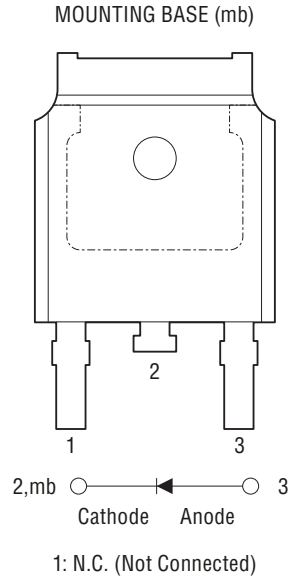
## Environmental Specifications

ESD Classification (HBM).....3B

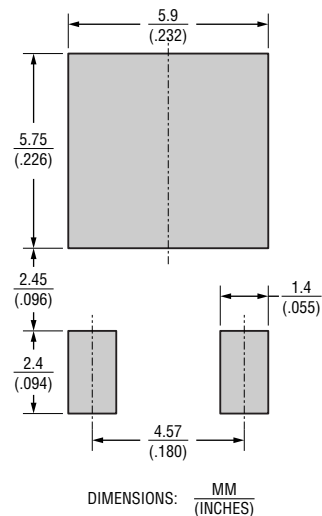
## How to Order

|                            | B     | S | D | 10 | G | 65 | E | 2 |
|----------------------------|-------|---|---|----|---|----|---|---|
| Manufacturer               | _____ |   |   |    |   |    |   |   |
| B = Bourns                 | _____ |   |   |    |   |    |   |   |
| Product Type               | _____ |   |   |    |   |    |   |   |
| SD = SiC Diodes            | _____ |   |   |    |   |    |   |   |
| Package Code               | _____ |   |   |    |   |    |   |   |
| D = TO252                  | _____ |   |   |    |   |    |   |   |
| Current Rating             | _____ |   |   |    |   |    |   |   |
| 10 = 10 A                  | _____ |   |   |    |   |    |   |   |
| Device Type                | _____ |   |   |    |   |    |   |   |
| G = General V <sub>F</sub> | _____ |   |   |    |   |    |   |   |
| Nominal Voltage            | _____ |   |   |    |   |    |   |   |
| 65 = 650 V                 | _____ |   |   |    |   |    |   |   |
| Configuration              | _____ |   |   |    |   |    |   |   |
| E = Single Diode           | _____ |   |   |    |   |    |   |   |
| Version Number             | _____ |   |   |    |   |    |   |   |

## Pin Information



## Recommended Footprint



Specifications are subject to change without notice.

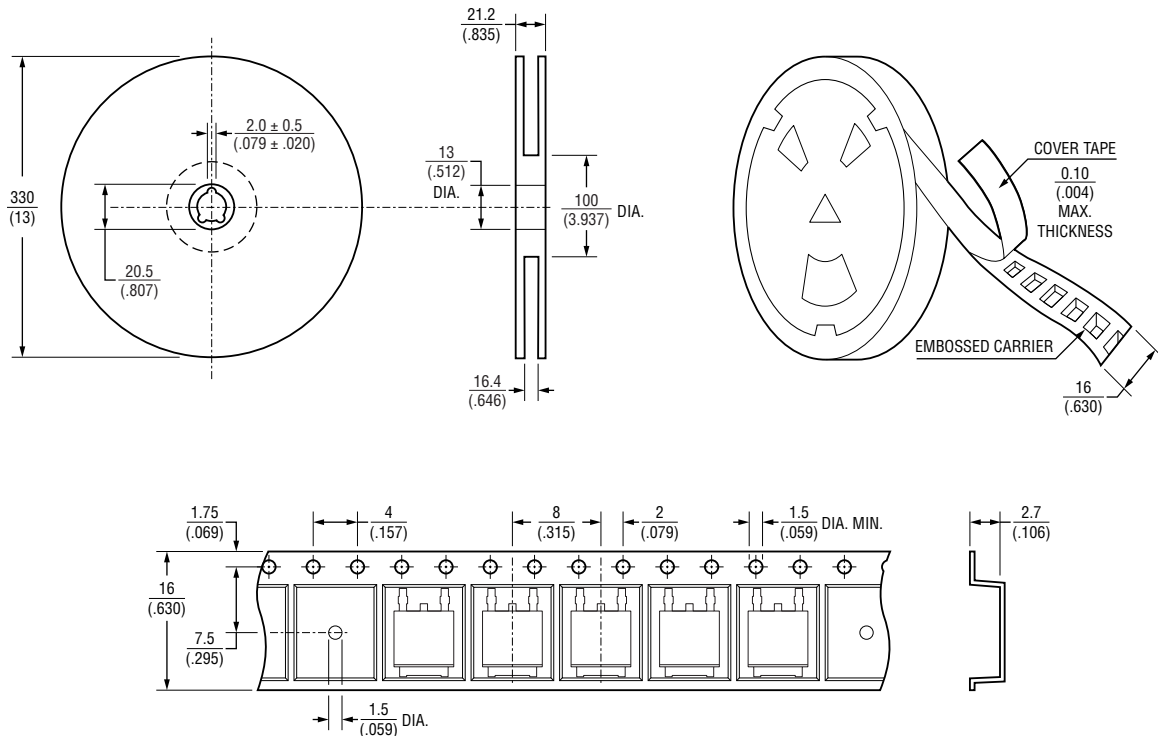
Users should verify actual device performance in their specific applications.

The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

# BSDD10G65E2 Silicon Carbide Schottky Diode

**BOURNS®**

## Packaging Specifications



DIMENSIONS:  $\frac{\text{MM}}{(\text{INCHES})}$

USER DIRECTION OF FEED →  
QTY: 2,500 PCS PER REEL

**BOURNS®**

Asia-Pacific: Tel: +886-2 2562-4117

Email: [asiacus@bourns.com](mailto:asiacus@bourns.com)

EMEA: Tel: +36 88 885 877

Email: [eurocus@bourns.com](mailto:eurocus@bourns.com)

The Americas: Tel: +1-951 781-5500

Email: [americus@bourns.com](mailto:americus@bourns.com)

[www.bourns.com](http://www.bourns.com)

REV. 08/23

Specifications are subject to change without notice.

Users should verify actual device performance in their specific applications.

The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [SiC Schottky Diodes](#) category:*

*Click to view products by [Bourns](#) manufacturer:*

Other Similar products are found below :

[C3D02060F](#) [C3D04060F](#) [C3D04065E](#) [C3D06060F](#) [C3D10060G](#) [C4D02120A](#) [C4D20120D](#) [C3D03060A](#) [C3D04060A](#) [C3D08065A](#)  
[C3D10060A](#) [C3D10065A](#) [C3D16060D](#) [C4D10120D](#) [C3D08065I](#) [C3D20065D](#) [C4D10120A](#) [C4D15120A](#) [C4D20120A](#) [C4D30120D](#)  
[C4D40120D](#) [BSDD10S65E6](#) [BSDH06G65E2](#) [BSDH10S65E6](#) [DSC04A065LP-13](#) [DSC04C065LP-13](#) [DSC06A065LP-13](#) [DSC08A065LP-13](#)  
[DSC10A065LP-13](#) [SI20C065D2](#) [SI20C065CD2](#) [SICW20C065](#) [GD25MPS17H](#) [GD30MPS12H](#) [GD50MPS12H](#) [GD05MPS17H](#)  
[GD02MPS12E](#) [GD10MPS12A](#) [GD2X75MPS17N](#) [GE04MPS06A](#) [GD10MPS12E](#) [GE04MPS06E-TR](#) [GE06MPS06E-TR](#) [GE08MPS06E-TR](#)  
[GE10MPS06E-TR](#) [GE12MPS06A](#) [GE12MPS06E-TR](#) [GE04MPS06Q-TR](#) [GE06MPS06Q-TR](#) [GE08MPS06Q-TR](#)